



# STPS40L15CW/CT

## LOW DROP OR-ing POWER SCHOTTKY DIODE

### MAJOR PRODUCT CHARACTERISTICS

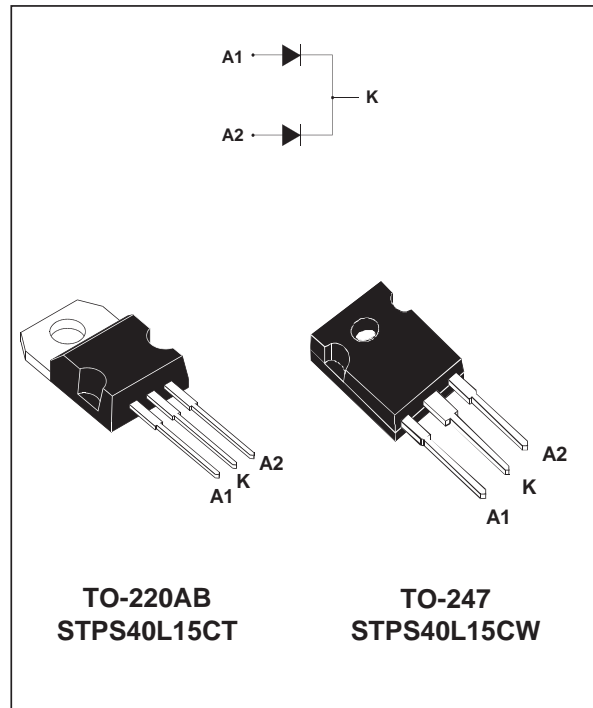
$I_{F(AV)}$	2 x 20 A
$V_{RRM}$	15 V
$T_j(\text{max})$	125°C
$V_F(\text{max})$	0.33 V

### FEATURES AND BENEFITS

- VERY LOW FORWARD VOLTAGE DROP FOR LESS POWER DISSIPATION AND REDUCED HEATSINK SIZE
- REVERSE VOLTAGE SUITED TO OR-ing OF 3V, 5V and 12V RAILS
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

Dual center tap schottky rectifier packaged in TO-220AB and TO-247, this device is especially intended for use as OR-ing diode in fault tolerant power supply equipments.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage		15	V	
$I_{F(RMS)}$	RMS forward current		30	A	
$I_{F(AV)}$	Average forward current	$T_{case} = 140^\circ\text{C}$	Total	40	A
		$\delta = 1$	Per diode	20	
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	310	A	
$I_{RRM}$	Peak repetitive reverse current	$t_p = 2 \mu\text{s}$ $F = 1\text{kHz}$	2	A	
$I_{RSM}$	Non repetitive peak reverse current	$t_p = 100 \mu\text{s}$	3	A	
$P_{ARM}$	Repetitive peak avalanche power	$t_p = 1 \mu\text{s}$ $T_j = 25^\circ\text{C}$	13140	W	
$T_{stg}$	Storage temperature range		- 65 to + 150	°C	
$T_j$	Maximum operating junction temperature *		125	°C	
$dV/dt$	Critical rate of rise of reverse voltage		10000	V/ $\mu\text{s}$	

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

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## THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.6	$^{\circ}\text{C}/\text{W}$
		Total	0.85	
$R_{th(c)}$	Coupling		0.1	$^{\circ}\text{C}/\text{W}$

## STATIC ELECTRICAL CHARACTERISTICS (Per diode)

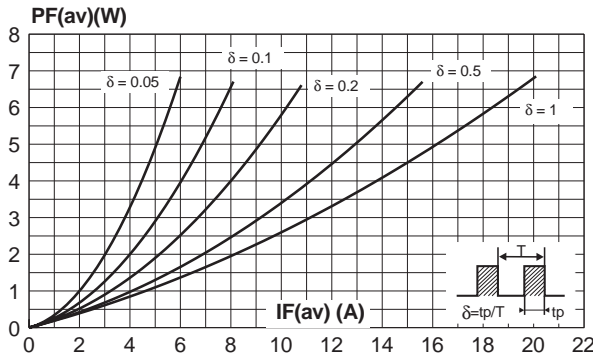
Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			6	mA
		$T_j = 100^{\circ}\text{C}$			200	500	
$V_F^*$	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 19\text{ A}$			0.41	V
		$T_j = 25^{\circ}\text{C}$	$I_F = 40\text{ A}$			0.52	
		$T_j = 125^{\circ}\text{C}$	$I_F = 19\text{ A}$		0.28	0.33	
		$T_j = 125^{\circ}\text{C}$	$I_F = 40\text{ A}$		0.42	0.50	

Pulse test : \*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

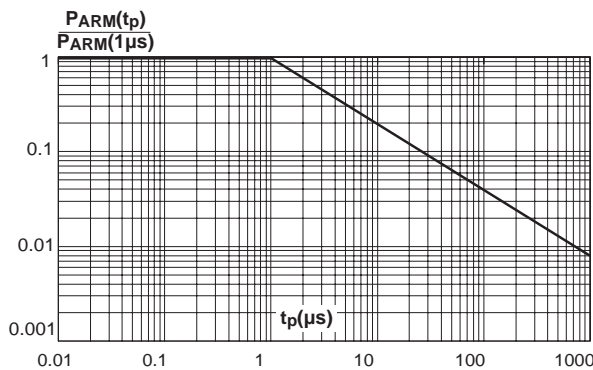
To evaluate the conduction losses use the following equation :

$$P = 0.18 \times I_{F(AV)} + 0.008 I_{F(RMS)}^2$$

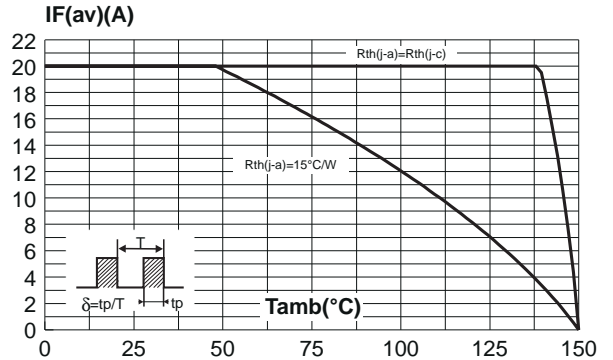
**Fig. 1:** Average forward power dissipation versus average forward current (per diode).



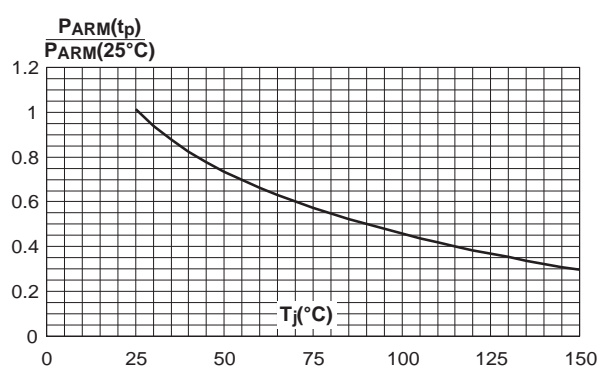
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



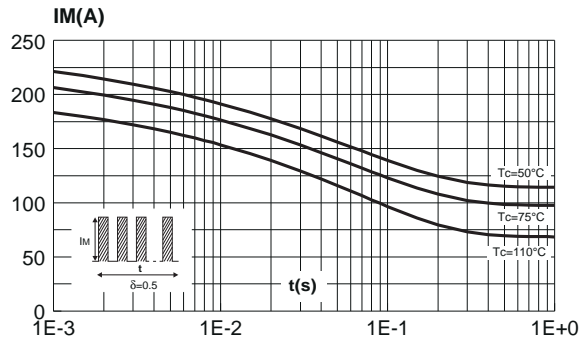
**Fig. 2:** Average forward current versus ambient temperature ( $\delta=1$ , per diode).



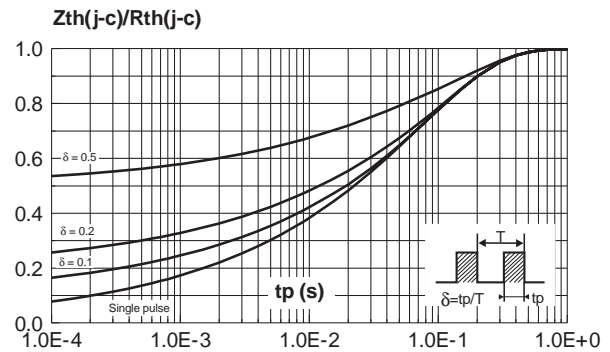
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



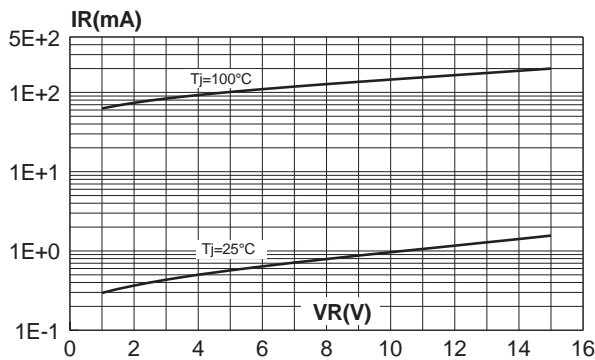
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values per diode).



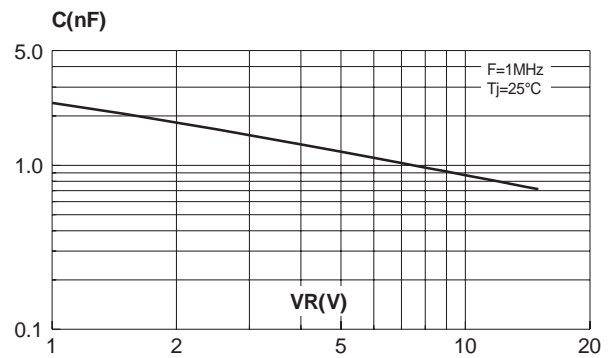
**Fig. 6:** Relative variation of thermal impedance junction to case versus pulse duration (per diode).



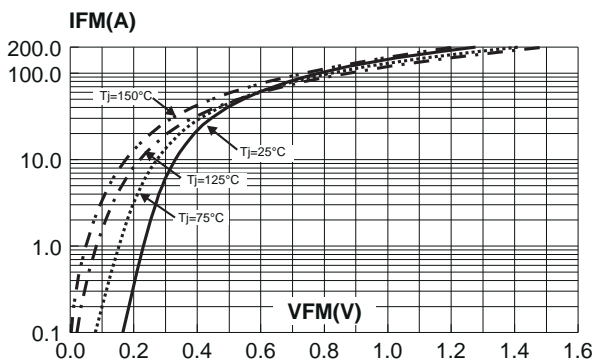
**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values per diode).



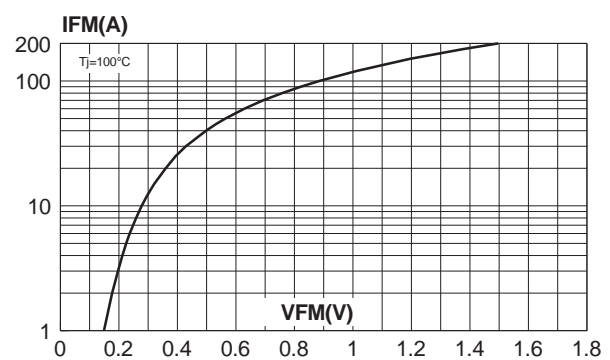
**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values per diode).



**Fig. 9:** Forward voltage drop versus forward current (typical values per diode).

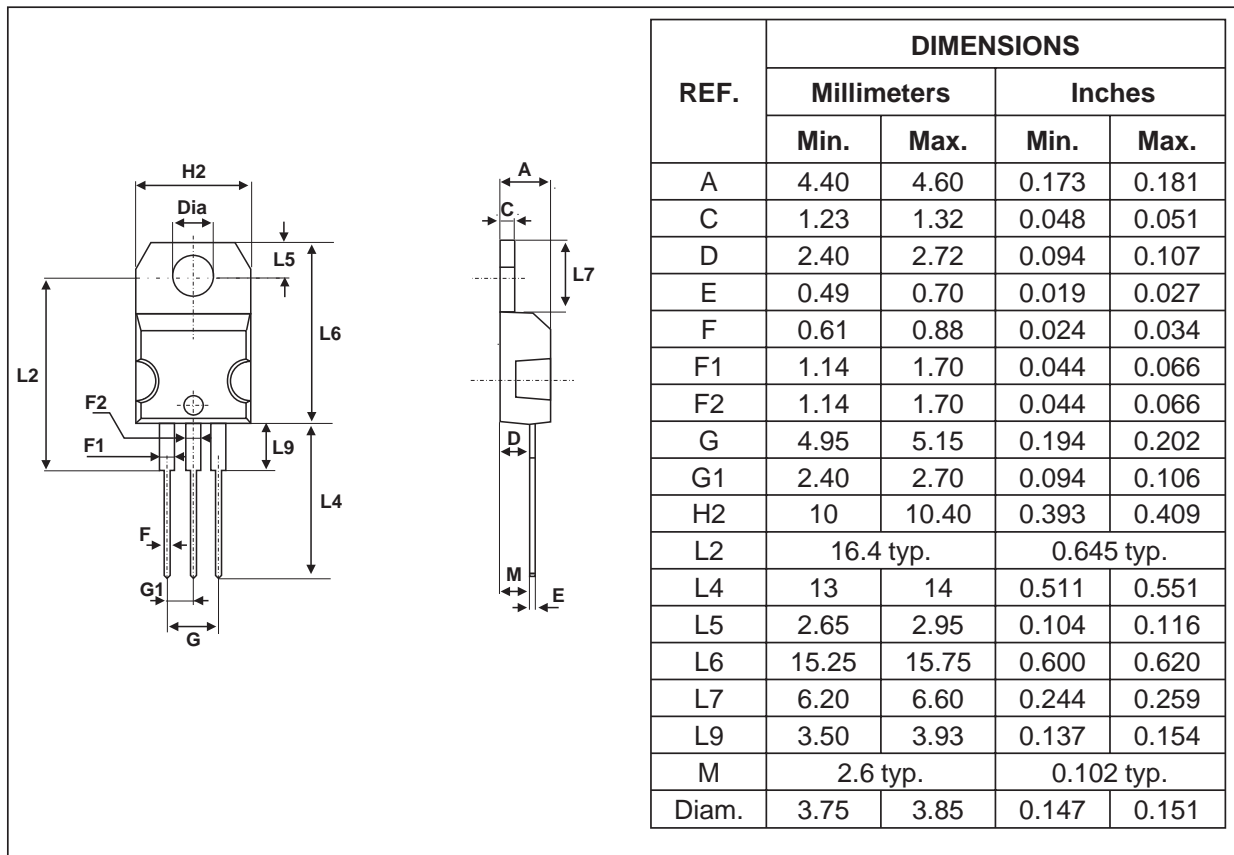


**Fig. 10:** Forward voltage drop versus forward current (typical maximum per diode).



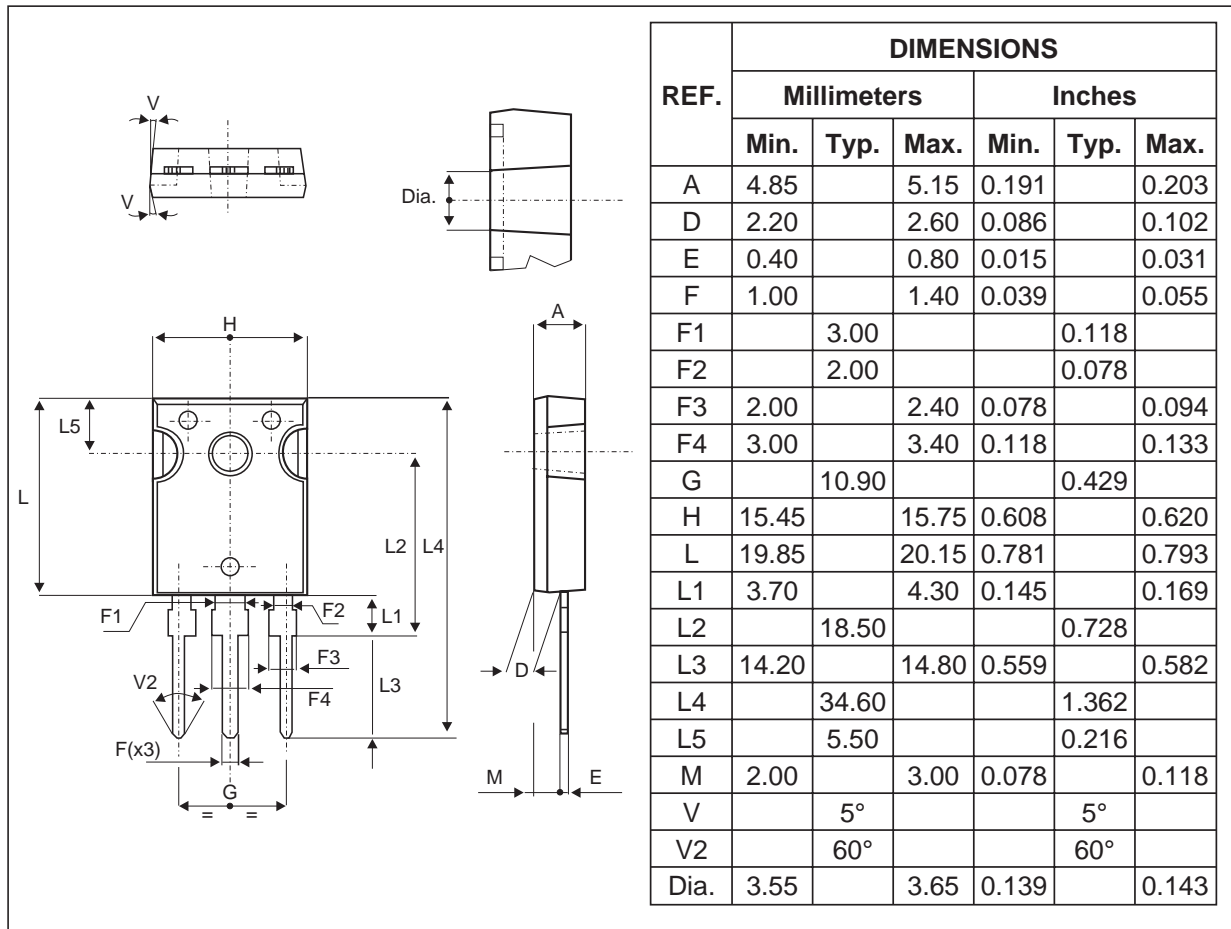
# STPS40L15CW/CT

## PACKAGE MECHANICAL DATA TO-220AB



- Cooling method: C
- Recommended torque value: 0.55 m.N
- Maximum torque value: 0.70 m.N

**PACKAGE MECHANICAL DATA**  
TO-247



- Cooling method: C
- Recommended torque value: 0.8 m.N
- Maximum torque value: 1.0 m.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS40L15CW	STPS40L15CW	TO-247	4.4 g.	30	Tube
STPS40L15CT	STPS40L15CT	TO-220AB	2g	50	Tube

- Epoxy meets UL94,V0

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